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# JFET - VHF/UHF Amplifier **Transistor**

## **N-Channel**

#### **Features**

- Drain and Source are Interchangeable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and **PPAP** Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	25	Vdc
Gate-Source Voltage	V <sub>GS</sub>	25	Vdc
Gate Current	I <sub>G</sub>	10	mAdc

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

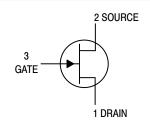
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.



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SOT-23 (TO-236) **CASE 318** STYLE 10

### MARKING DIAGRAM



6x = Device Code

x = U for MMBFJ309L, SMMBFJ309L

x = T for MMBFJ310L, SMMBFJ310L

= Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MMBFJ309LT1G,	SOT-23	3,000 / Tape &
SMMBFJ309LT1G	(Pb-Free)	Reel
MMBFJ310LT1G,	SOT-23	3,000 / Tape &
SMMBFJ310LT1G	(Pb-Free)	Reel
SMMBFJ310LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

TELECTRICAL CHARACTERIOTICS (TA = 25 of unices) officerwise noted)							
Characteristic	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS							
Gate–Source Breakdown Voltage $(I_G = -1.0 \mu Adc, V_{DS} = 0)$	V <sub>(BR)GSS</sub>	-25	-	_	Vdc		
Gate Reverse Current ( $V_{GS} = -15 \text{ Vdc}$ ) ( $V_{GS} = -15 \text{ Vdc}$ , $T_A = 125^{\circ}\text{C}$ )	I <sub>GSS</sub>	_ _	- -	-1.0 -1.0	nAdc μAdc		
	V <sub>GS(off)</sub>	-1.0 -2.0	- -	-4.0 -6.5	Vdc		
ON CHARACTERISTICS							
	I <sub>DSS</sub>	12 24	- -	30 60	mAdc		
Gate-Source Forward Voltage (I <sub>G</sub> = 1.0 mAdc, V <sub>DS</sub> = 0)	V <sub>GS(f)</sub>	-	-	1.0	Vdc		
SMALL-SIGNAL CHARACTERISTICS	-		•				
Forward Transfer Admittance (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 10 mAdc, f = 1.0 kHz)	Y <sub>fs</sub>	8.0	-	18	mmhos		
Output Admittance $(V_{DS} = 10 \text{ Vdc}, I_D = 10 \text{ mAdc}, f = 1.0 \text{ kHz})$	y <sub>os</sub>	_	-	250	μmhos		
Input Capacitance (V <sub>GS</sub> = -10 Vdc, V <sub>DS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>iss</sub>	_	-	5.0	pF		
Reverse Transfer Capacitance (V <sub>GS</sub> = -10 Vdc, V <sub>DS</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>rss</sub>	_	-	2.5	pF		
Equivalent Short–Circuit Input Noise Voltage (V <sub>DS</sub> = 10 Vdc, I <sub>D</sub> = 10 mAdc, f = 100 Hz)	<del>e</del> n	-	10	-	nV/√Hz		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

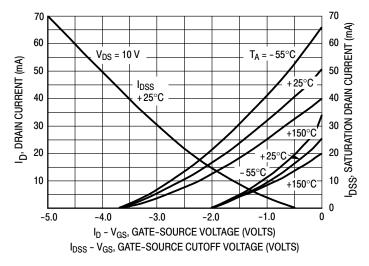


Figure 1. Drain Current and Transfer Characteristics versus Gate-Source Voltage

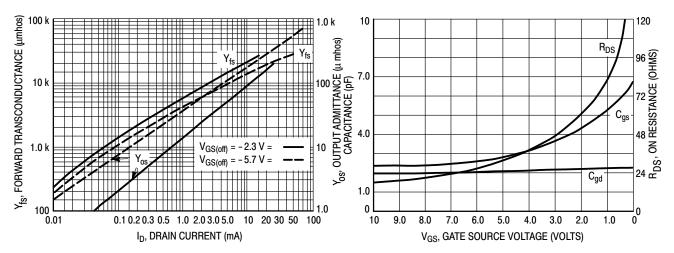


Figure 2. Common–Source Output Admittance and Forward Transconductance versus Drain Current

Figure 3. On Resistance and Junction Capacitance versus Gate-Source Voltage

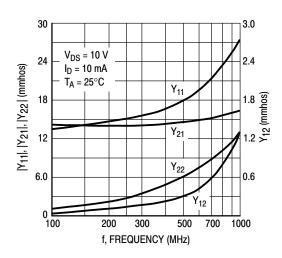


Figure 4. Common-Gate Y Parameter Magnitude versus Frequency

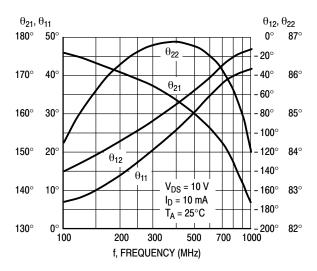


Figure 6. Common–Gate Y Parameter Phase–Angle versus Frequency

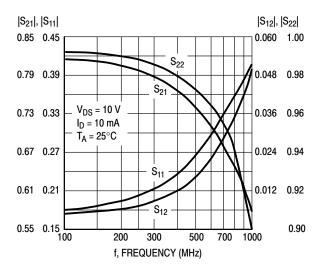


Figure 5. Common-Gate S Parameter Magnitude versus Frequency

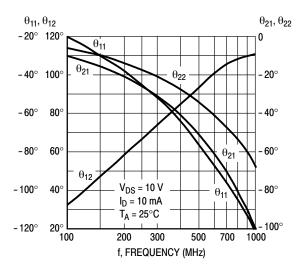
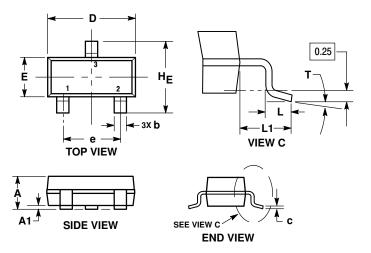


Figure 7. S Parameter Phase–Angle versus Frequency

## PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR** 



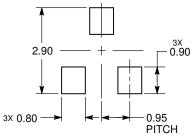
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

STYLE 10:

- PIN 1. DRAIN
  - SOURCE 2.
  - GATE

## **RECOMMENDED** SOLDERING FOOTPRINT\*



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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